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FOD819 4-Pin DIP High Speed Phototransistor Optocouplers

Description

The FOD819 consists of a gallium arsenide (GaAs) infra— red emitting diode, driving a high speed photo detector with integrated base—to—emitter resistor, R_{BE} , in a 4—pin dual—in—line package. It is designed to be an improved replacement to the popular FOD817 Series when higher speed performance is required in isolated data signal transmission.

Features

- High Speed Performance ~ 30 kHz
- Current Transfer Ratio: 100% to 600%
- Minimum BV_{CEO} of 80 V Guaranteed
- Safety and Regulatory Approvals:
- UL1577, 5,000 VAC_{RMS} for 1 Minute
- DIN EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Typical Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- Twisted Pair Line Receiver
- Telephone Line Receiver



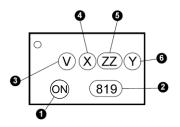
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DIP 4 PINS

MARKING DIAGRAM



1. ON = Company Logo

2. 819 = Device Number

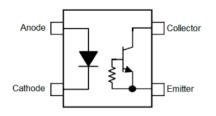
3. V = DIN EN/IEC60747-5-5 Option

4 X = One-Digit Year Code

5. ZZ = Digit Work Week

6. Y = Assembly Package Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

Safety and Insulation Ratings

As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Table 1. SAFETY AND INSULATION RATINGS

| Parameter | | Characteristics |
|--|------------------------|-----------------|
| | < 150 V _{RMS} | I–IV |
| 0110/1.89 Table 1, For Rated Mains Voltage | < 300 V _{RMS} | I–III |
| Climatic Classification | | 55/115/21 |
| Pollution Degree (DIN VDE 0110/1.89) | | 2 |
| Comparative Tracking Index | | 175 |

Table 2.

| Symbol | Parameter | Value | Unit |
|----------------|--|--------------------|-------|
| VPR | Input–to–Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10 \text{ s}$, Partial Discharge < 5 pC | 1360 | Vpeak |
| | Input–to–Output Test Voltage, Method B, $V_{IORM} x$ 1.875 = V_{PR} , 100% Production Test with t_m = 1 s, Partial Discharge < 5 pC | 1594 | Vpeak |
| VIORM | Maximum Working Insulation Voltage | 850 | Vpeak |
| VIOTM | Highest Allowable Over–Voltage | 8000 | Vpeak |
| | External Creepage | ≥ 7 | mm |
| | External Clearance | ≥ 7 | mm |
| | External Clearance (for Option W, 0.4" Lead Spacing) | ≥ 10 | mm |
| DTI | Distance Through Insulation (Insulation Thickness) | ≥ 0.4 | mm |
| T _S | Case Temperature (Note 1) | 175 | °C |
| IS,INPUT | Input Current (Note 1) | 400 | mA |
| PS,OUTPUT | Output Power (Note 1) | 700 | mW |
| RIO | Insulation Resistance at T _S , V _{IO} = 500 V (Note 1) | > 10 ¹¹ | Ω |

^{1.} Safety limit values – maximum values allowed in the event of a failure.

Table 3. ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|-------------------------------------|--------------------|-------|
| TOTAL PACKAGE | | | |
| T _{STG} | Storage Temperature | -55 to +125 | °C |
| T _{OPR} | Operating Temperature | -55 to +110 | °C |
| T _J | Junction Temperature | -55 to +125 | °C |
| T _{SOL} | Lead Solder Temperature | 260 for 10 seconds | °C |
| θJC | Junction-to-Case Thermal Resistance | 210 | °C/W |
| P _{TOT} | Total Device Power Dissipation | 200 | mW |
| EMITTER | | | |
| I _F | Continuous Forward Current | 50 | mA |
| V _R | Reverse Voltage | 6 | V |
| P _D | Power Dissipation | 70 | mW |
| 10 | Derate Above 100°C | 1.7 | mW/°C |

Table 3. ABSOLUTE MAXIMUM RATINGS (continued)

| Symbol | Parameter | Value | Unit | | | |
|------------------|------------------------------|-------|-------|--|--|--|
| DETECTOR | DETECTOR | | | | | |
| V _{CEO} | Collector–Emitter Voltage | 80 | V | | | |
| V _{ECO} | Emitter–Collector Voltage | 2 | V | | | |
| I _C | Continuous Collector Current | 30 | mA | | | |
| P _C | Collector Power Dissipation | 150 | mW | | | |
| 1 0 | Derate Above 90°C | 2.9 | mW/°C | | | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

 $\textbf{Table 4. INDIVIDUAL COMPONENT CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ specified)$

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|----------------------|-------------------------------------|---|------|------|------|------|
| EMITTER | R | | | • | • | • |
| V _F | Forward Voltage | I _F = 1.5 mA | | 1.2 | 1.4 | V |
| I _R | Reverse Current | V _R = 4.0 V | | | 10 | μΑ |
| Ct | Terminal Capacitance | V = 0, f = 1 kHz | | 30 | | pF |
| DETECT | OR | | | | | |
| I _{CEO} | Collector Dark Current | V _{CE} = 40 V, I _F = 0 | | | 100 | nA |
| BV _{CEO} | Collector–Emitter Breakdown Voltage | $I_C = 0.1 \text{ mA}, I_F = 0$ | 80 | 150 | | V |
| BV _{ECO} | Emitter-Collector Breakdown Voltage | $I_E = 0.1 \text{ mA}, I_F = 0$ | 2 | 7 | | V |
| DC TRAN | ISFER CHARACTERISTICS | | | | | |
| CTR | Current Transfer Ratio (Note 2) | $I_F = 1.5 \text{ mA}, V_{CE} = 5 \text{ V}$ | 100 | | 600 | % |
| V _{CE(SAT)} | Saturation Voltage | $I_F = 1.5 \text{ mA}, I_C = 0.2 \text{ mA}$ | | | 0.3 | V |
| I _{C(OFF)} | OFF-state collector current | $V_F = 0.7 \text{ V}, V_{CE} = 40 \text{ V}$ | | | 10 | μΑ |
| AC TRAN | ISFER CHARACTERISTICS | | | | | |
| t _R | Rise Time (Saturated) | I_F = 1.5 mA, V_{CC} = 5 V, R_L = 10 k Ω | | 12 | | μs |
| t _F | Fall Time (Saturated) | (Note 3) | | 20 | | μs |
| t _{PHL} | Propagation Delay Time High-to-Low | I_F = 1.5 mA, V_{CC} = 5 V, R_L = 10 k Ω | | 9 | 30 | μs |
| t _{PLH} | Propagation Delay Time Low-to-High | (Note 3) | | 18 | 30 | μs |

Current Transfer Ratio (CTR) = I_C / I_F x 100%.
Refer to test circuit setup.

Table 5. ISOLATION CHARACTERISTICS ($T_A = 25$ °C unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|------------------|---|---|------|----------------------|------|--------------------|
| V _{ISO} | Input-Output Isolation Voltage (Note 4) | $f = 60$ Hz, $t = 1$ minutes, $I_{I-O} \le 2 \mu A$ | 5000 | | | VAC _{RMS} |
| R _{ISO} | Isolation Resistance | $V_{I-O} = 500 V_{DC}$ | | 1 x 10 ¹¹ | | Ω |
| C _{ISO} | Isolation Capacitance | $V_{I-O} = 0$, $f = 1 \text{ MHz}$ | | 0.6 | 1.0 | pf |

^{4.} For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

Typical Performance Curves

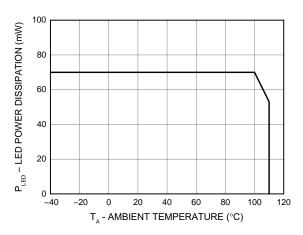


Figure 1. LED Power Dissipation vs. Ambient Temperature

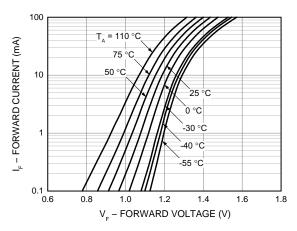


Figure 3. Forward Current vs. Forward Voltage

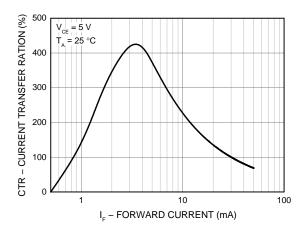


Figure 5. Current Transfer Ratio vs. Forward Current

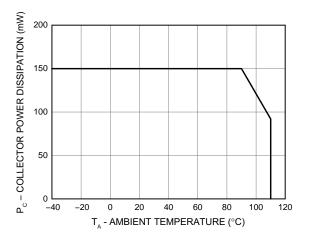


Figure 2. Collector Power Dissipation vs. Ambient Temperature

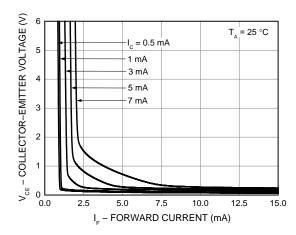


Figure 4. Collector-Emitter Voltage vs. Forward Current

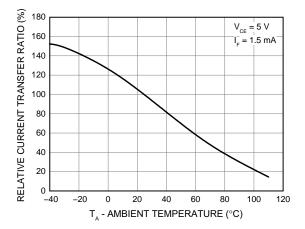


Figure 6. Relative Current Transfer Ratio vs. Ambient Temperature

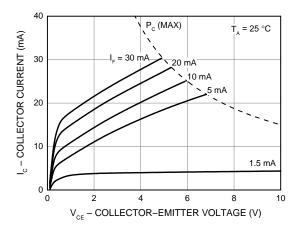


Figure 7. Collector Current vs. Collector-Emitter Voltage

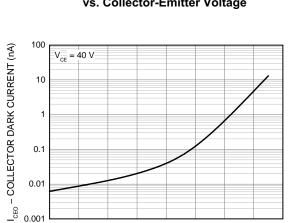


Figure 9. Collector Dark Current vs. Ambient Temperature

T_A - AMBIENT TEMPERATURE (°C)

0

20

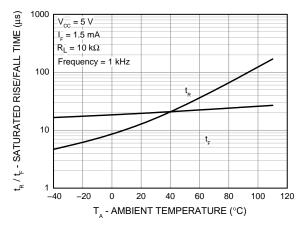


Figure 11. Saturated Rise / Fall Time vs. Ambient Temperature

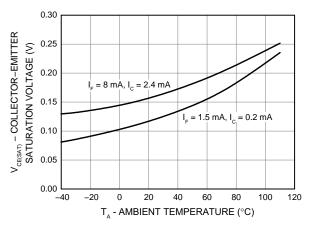


Figure 8. Collector-Emitter Saturation Voltage vs. Ambient Temperature

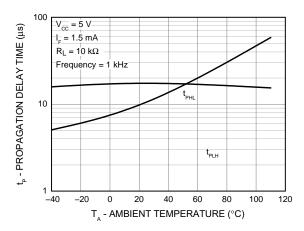


Figure 10. Propagation Delay vs. Ambient Temperature

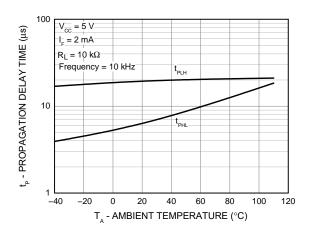


Figure 12. Propagation Delay vs. Ambient Temperature

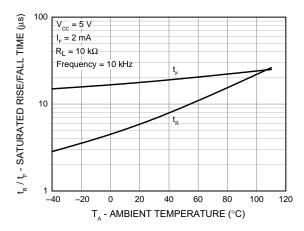


Figure 13. Collector Dark Current vs. Ambient Temperature

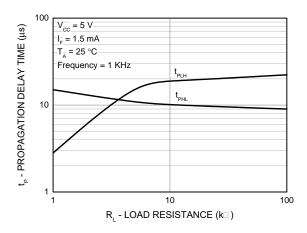


Figure 14. Propagation Delay vs. Ambient Temperature

Test Circuit

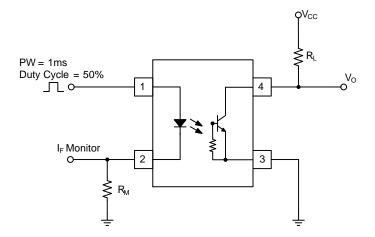


Figure 15. Test Circuit for Response Time

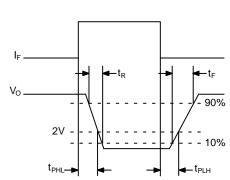


Figure 16. Timing Diagram

Reflow Profile

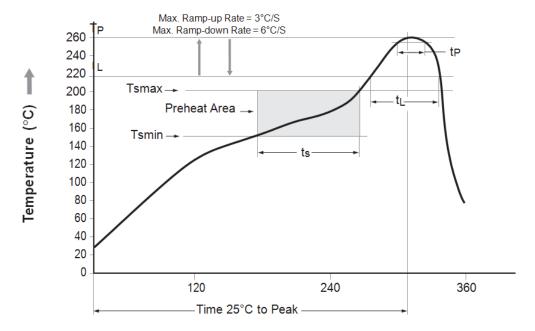


Figure 17. Reflow Profile

Table 6.

| Profile Freature | Pb-Free Assembly Profile |
|---|--------------------------|
| Temperature Min. (Tsmin) | 150°C |
| Temperature Max. (Tsmax) | 200°C |
| Time (t _S) from (Tsmin to Tsmax) | 60–120 seconds |
| Ramp-up Rate (t _L to t _P) | 3°C/second max. |
| Liquidous Temperature (T _L) | 217°C |
| Time (t _L) Maintained Above (T _L) | 60–150 seconds |
| Peak Body Package Temperature | 260°C +0°C / -5°C |
| Time (t _P) within 5°C of 260°C | 30 seconds |
| Ramp-down Rate (T _P to T _L) | 6°C / second max. |
| Time 25°C to Peak Temperature | 8 minutes max. |

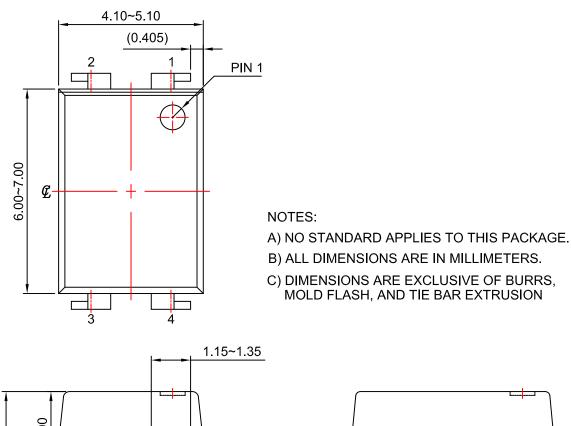
Table 7. ORDERING INFORMATION

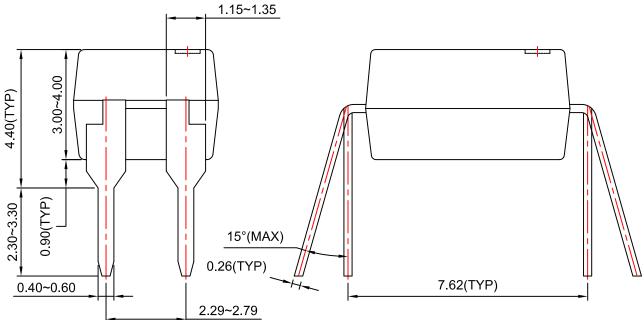
| Part Number | Package | Packing Method † |
|-------------|--|--------------------------------------|
| FOD819 | DIP 4–Pin | Tube (100 units per tube) |
| FOD819S | SMT 4-Pin (Lead Bend) | Tube (100 units per tube) |
| FOD819SD | SMT 4-Pin (Lead Bend) | Tape and Reel (1,000 units per reel) |
| FOD819300 | DIP 4-Pin, DIN EN/IEC60747-5-5 option | Tube (100 units per tube) |
| FOD8193S | SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option | Tube (100 units per tube) |
| FOD8193SD | SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option | Tape and Reel (1,000 units per reel) |
| FOD819300W | DIP 4-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 option | Tube (100 units per tube) |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

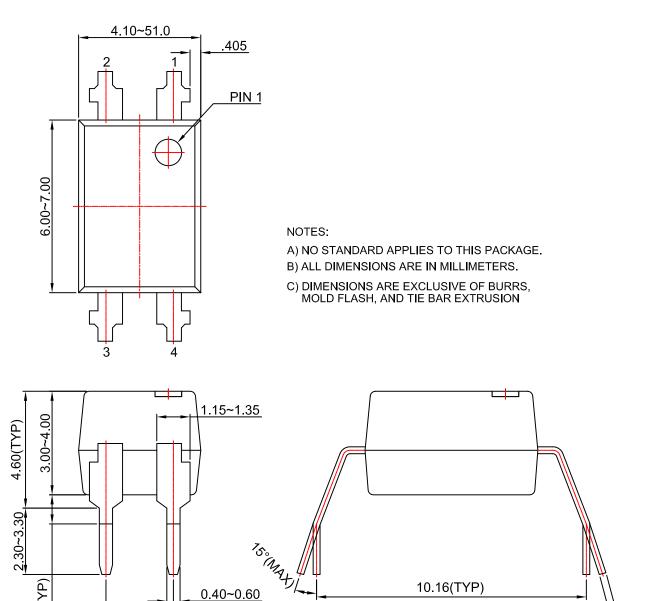
PACKAGE DIMENSIONS

PDIP4 4.6 x 6.5, 2.54P CASE 646CD ISSUE O





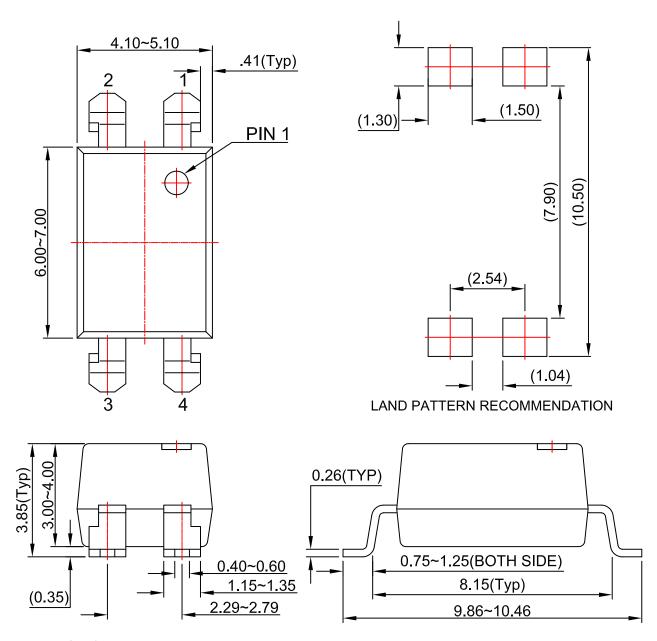
PDIP4 4.6 x 6.5, 2.54P CASE 646CA ISSUE O



.26(TYP)

2.29~2.79

PDIP4 GW CASE 709AH ISSUE A



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION

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